

Specifications

Absolute Maximum Ratings at Ta = 25°C

Parameter	Symbol	Conditions	Ratings	Unit
Drain-to-Source Voltage	V _{DSS}		20	V
Gate-to-Source Voltage	V _{GSS}		±10	V
Drain Current (DC)	۱ _D		4	A
Drain Current (Pulse)	I _{DP}	PW≤10µs, duty cycle≤1%	16	A
Allowable Power Dissipation	PD	Tc=25°C	20	W W
Channel Temperature	Tch	<i>}</i>	150,	C C
Storage Temperature	Tstg		_55 to +150	°C
Electrical Characteristics at Ta = 25°C			<u>.</u>	•

Electrical Characteristics at Ta = 25°C

			59.86°			
Parameter	Symbol	Conditions	min	Ratings/ typ	max	Unit
Drain-to-Source Breakdown Voltage	V(BR)DSS	I _D =1mA, V _{GS} =0	20	and the second second		V
Zero-Gate Voltage Drain Current	IDSS	V _{DS} =16V, V _{GS} =0		and a support	100	μA
Gate-to-Source Leakage Current	IGSS	V _{GS} =±8V, V _{DS} =0		and the second se	±10	μA
Cutoff Voltage	VGS(off)	V _{DS} =10V, I _D =1mA	0.5		1.5	V
Forward Transfer Admittance	yfs	V _{DS} =10V, I _D =2A	3.5	5		S
Static Drain-to-Source ON-State Resistance	R _{DS(on)}	I _D =2A, V _{GS} =4V	and the second	65	85	mΩ
Static Drain-to-Source On-State Resistance	R _{DS(on)}	I _D =1A, V _{GS} =2.5∜	all a second sec	85	125	mΩ
Input Capacitance	Ciss	V _{DS} =10V, f=1MHz		400		pF
Output Capacitance	Coss	V _{DS} =10V, f≡1MHz		300		pF
Reverse Transfer Capacitance	Crss	V _{DS} =10V, t⊭1MHz		160		pF
Turn-ON Delay Time	^t d(on)	See specified Test Circuit		20		ns
Rise Time	tr	See specified Test Circuit		70		ns
Turn-OFF Delay Time	^t d(off)	See specified Test Circuit		100		ns
Fall Time	t _f	See specified Test Circuit		120		ns
Diode Forward Voltage	V _{SD}	I _S =4A, √ _{GS} =0		1.0	1.2	V

Switching Time Test Circuit





